

Schottky Barrier Diode**MMBD330/MMBD770****FEATURES**

- Extremely low minority carrier lifetime.
- Very low capacitance.
- Low reverse leakage.



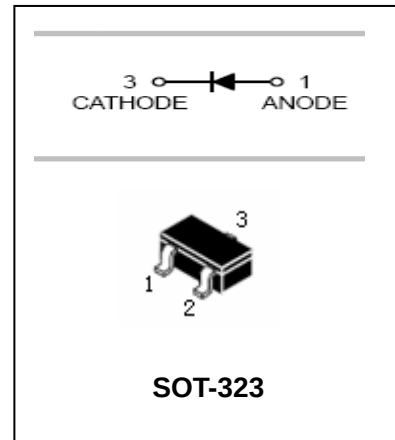
Lead-free

APPLICATIONS

- For high-efficiency UHF and VHF detector application.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMBD330	4T	SOT-323
MMBD770	5H	SOT-323

**MAXIMUM RATING @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Limits	Unit
Reverse voltage MMBD330 MMBD770	V_R	30 70	V
Forward Continuous Current (DC)	I_F	200	mA
Peak Forward Surge Current	I_{FSM}	1.0	A
Power Dissipation	P_d	120	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55-+150	°C

Schottky Barrier Diode

MMBD330/MMBD770

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse Breakdown voltage MMBD330 MMBD770	$V_{(BR)R}$	$I_R=100\mu A$	30 70		V
Reverse current MMBD330 MMBD770	I_R	$V_R=25V$ $V_R=35V$		200 200	nA
Forward voltage MMBD330 MMBD770	V_F	$I_F=1.0mA$ $I_F=10mA$ $I_F=1.0mA$ $I_F=10mA$		0.45 0.60 0.50 1.0	V
Diode capacitance MMBD330 MMBD770	C_D	$V_R=15V, f=1MHz$ $V_R=20V, f=1MHz$		0.9 0.5	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

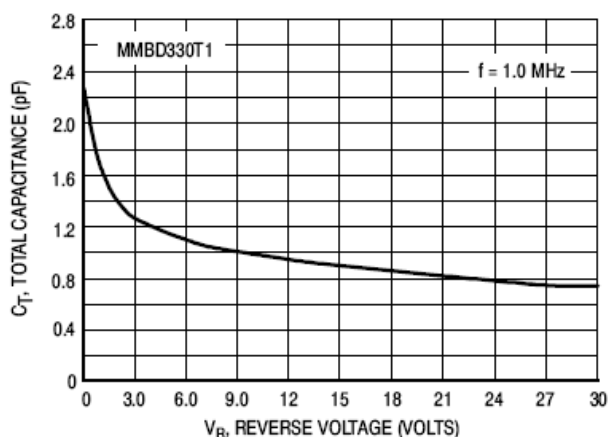


Figure 1. Total Capacitance

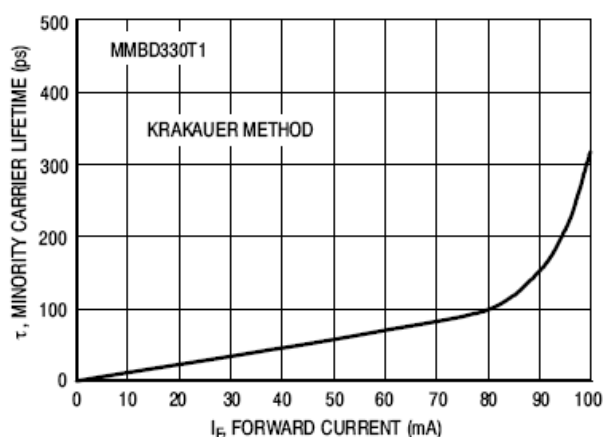


Figure 2. Minority Carrier Lifetime

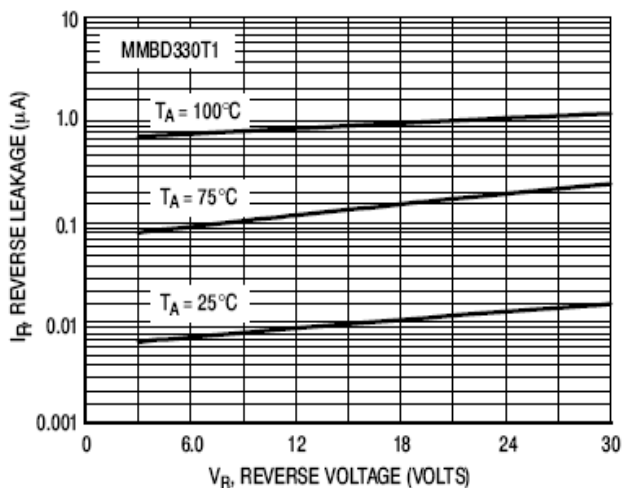


Figure 3. Reverse Leakage

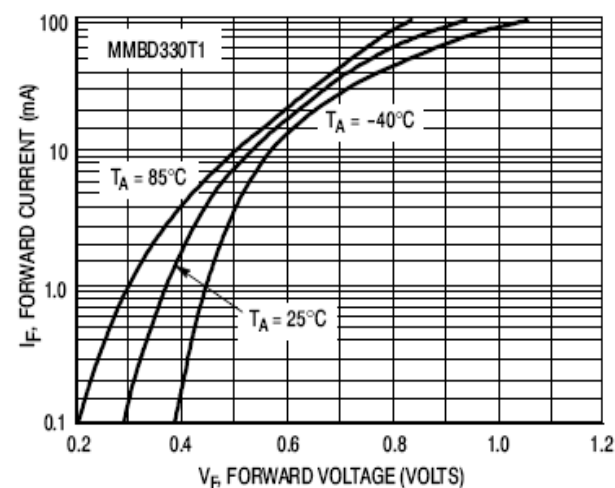


Figure 4. Forward Voltage

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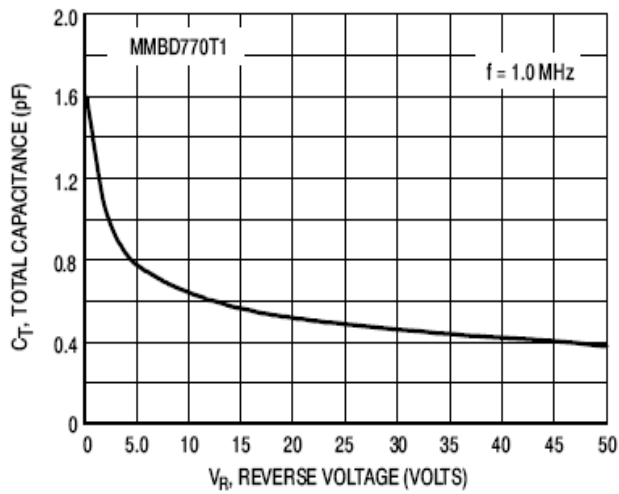


Figure 5. Total Capacitance

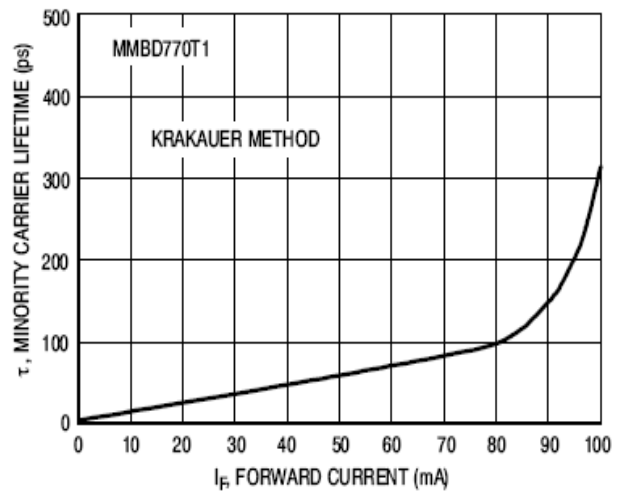


Figure 6. Minority Carrier Lifetime

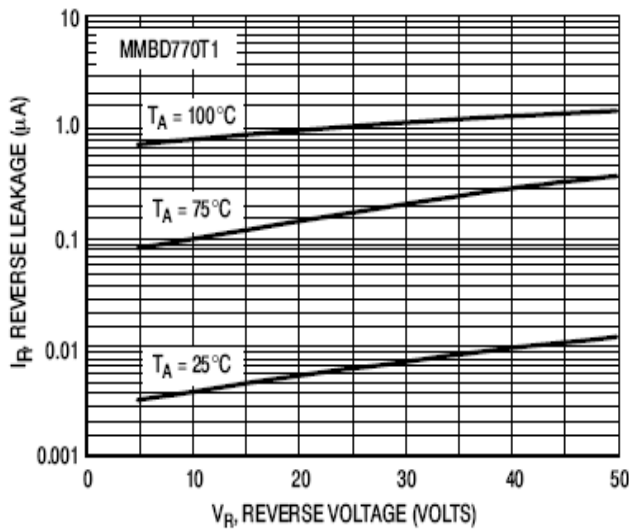


Figure 7. Reverse Leakage

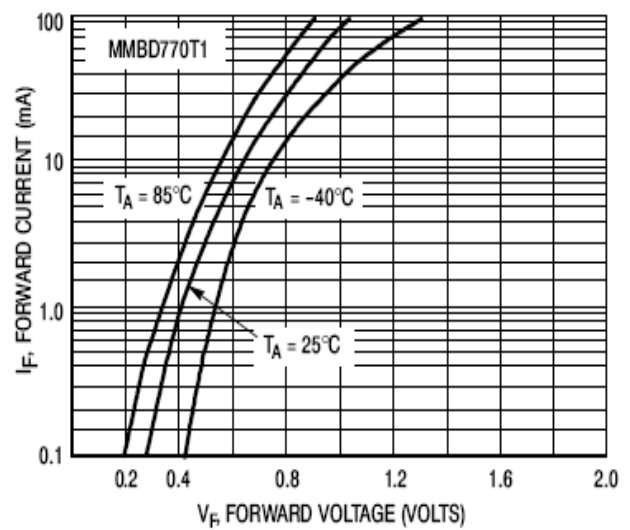


Figure 8. Forward Voltage

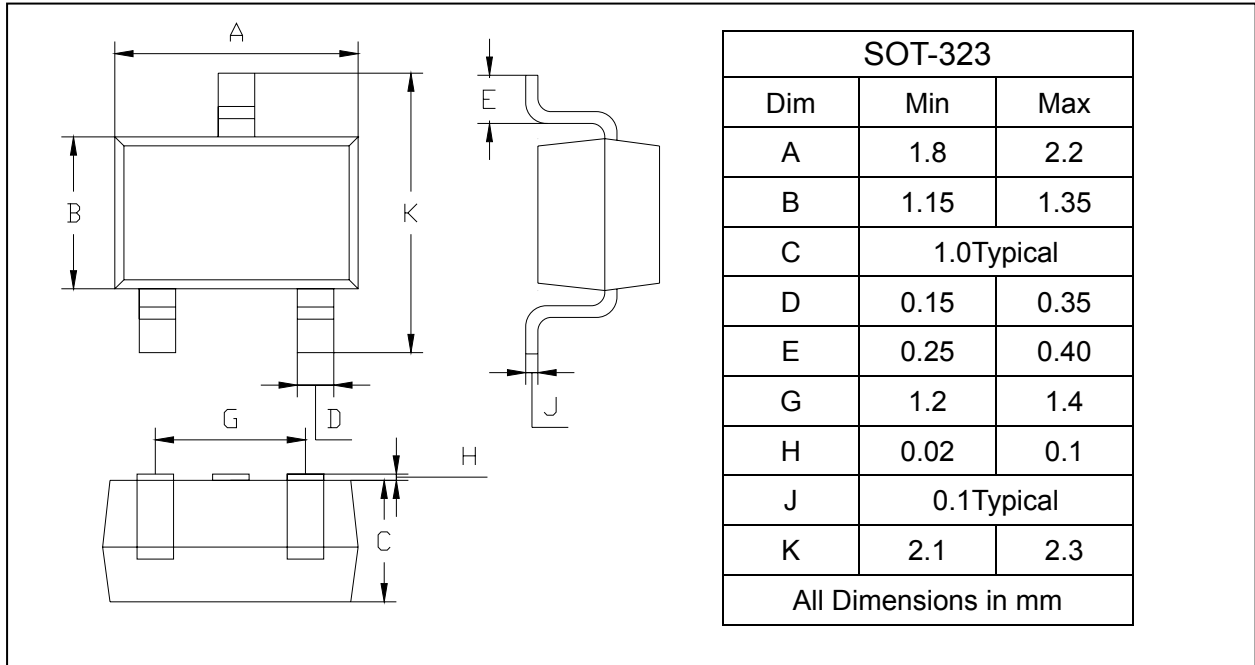
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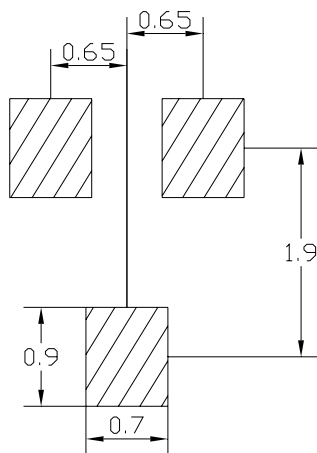
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
MMBD330/MMBD770	SOT-323	3000/Tape&Reel